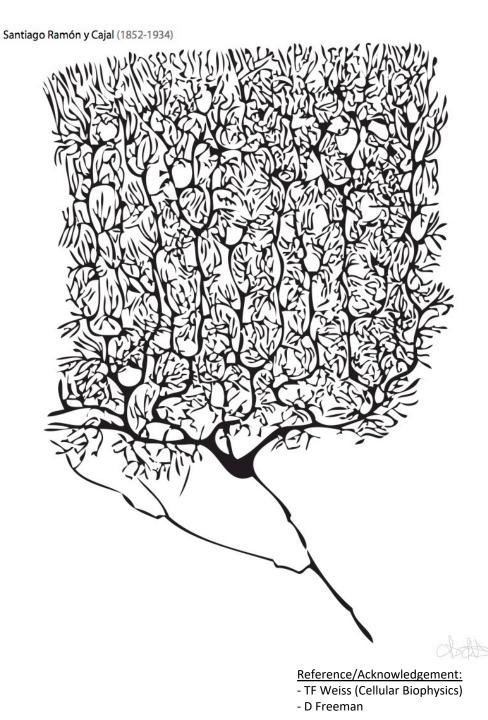
# **Cellular Electrodynamics**

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#### Website:

http://www.yorku.ca/cberge/4080W2020.html

York University Winter 2020 BPHS 4080 Lecture 18



$$\frac{1}{2\pi a(r_o + r_i)} \frac{\partial^2 V_m}{\partial z^2} = C_m \frac{\partial V_m}{\partial t} + G_K(V_m, t) (V_m - V_K) + G_{Na}(V_m, t) (V_m - V_{Na}) + G_L(V_m - V_L)$$

$$G_K(V_m, t) = \overline{G}_K n^4(V_m, t)$$

$$G_{Na}(V_m, t) = \overline{G}_{Na} m^3(V_m, t) h(V_m, t)$$

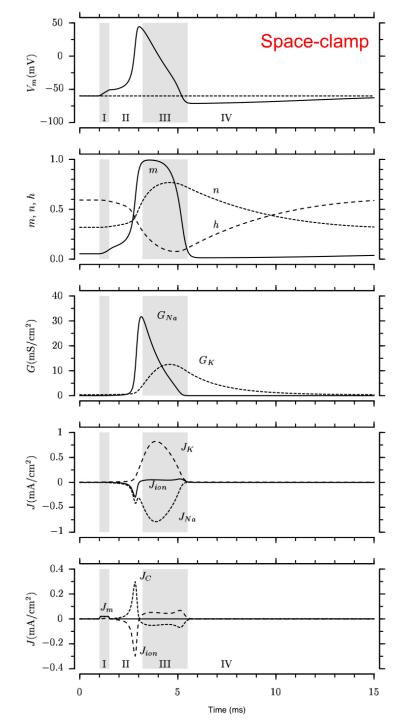
$$n(V_m, t) + \tau_n(V_m) \frac{dn(V_m, t)}{dt} = n_\infty(V_m)$$

$$m(V_m, t) + \tau_m(V_m) \frac{dm(V_m, t)}{dt} = m_\infty(V_m)$$

$$h(V_m, t) + \tau_h(V_m) \frac{dh(V_m, t)}{dt} = h_\infty(V_m)$$

$$\tau_{x}\frac{dx}{dt} + x = x_{\infty} \qquad \frac{dx}{dt} = \alpha_{x}(1-x) - \beta_{x}x$$
$$x_{\infty} = \alpha_{x}/(\alpha_{x} + \beta_{x}) \text{ and } \tau_{x} = 1/(\alpha_{x} + \beta_{x})$$

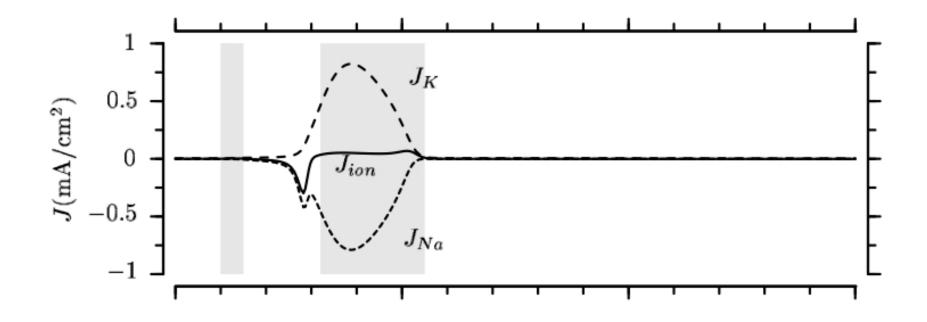
$$\begin{aligned} \alpha_m &= \frac{-0.1(V_m + 35)}{e^{-0.1(V_m + 35)} - 1}, \\ \beta_m &= 4e^{-(V_m + 60)/18}, \\ \alpha_h &= 0.07e^{-0.05(V_m + 60)}, \\ \beta_h &= \frac{1}{1 + e^{-0.1(V_m + 30)}}, \\ \alpha_n &= \frac{-0.01(V_m + 50)}{e^{-0.1(V_m + 50)} - 1}, \\ \beta_n &= 0.125e^{-0.0125(V_m + 60)}, \end{aligned}$$



#### Four phases:

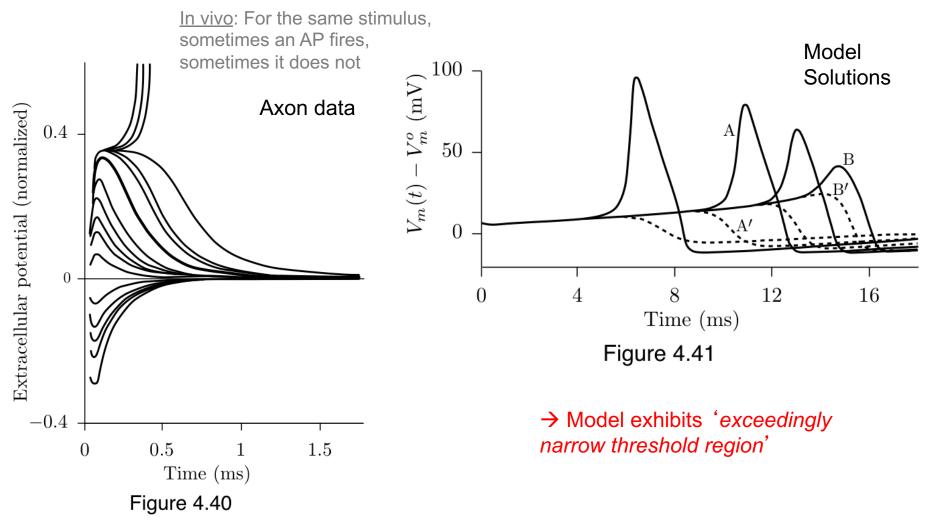
- 1. Local disturbance due to capacitance (behaves like cable model)
- 2. Onset:  $V_m$  change triggers m(increased  $G_{Na}$  take  $V_m$  with it)
- 3. Falloff: *h* turns off, *n* turns on (both work to lower  $V_m$  back towards  $V_k$ , basis for absolute refractory period)
- 4. Undershoot: increased  $G_k$  pushes  $V_m$ beyond  $V_m^o$ (basis for relative refractory period)

<u>Note</u>: Membrane current  $(J_M)$  can be parsed up into two components: a capacitive current  $(J_C)$  and an ionic current  $(J_{ion})$ 



<u>Note</u>: Fairly little net current across membrane (i.e., relatively few net ions transported)

#### **Threshold**

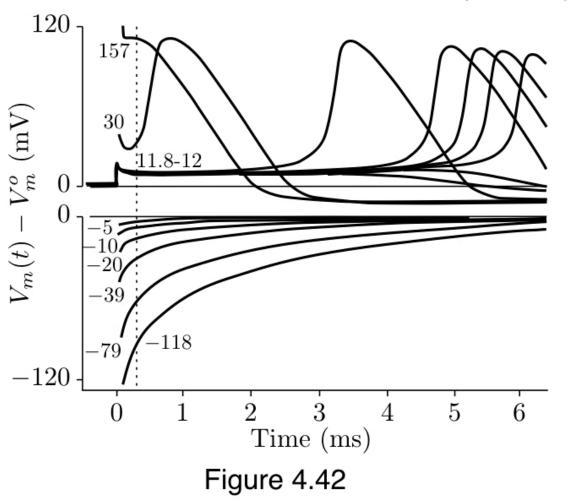


# → What is mechanism for a threshold?

<u>Note</u>: Model is deterministic and does not capture stochastic behaviors manifest in-vivo

**Threshold** 

```
Space-clamped
```



→ Note lag for AP to occur (stems from capacitive build-up to threshold)

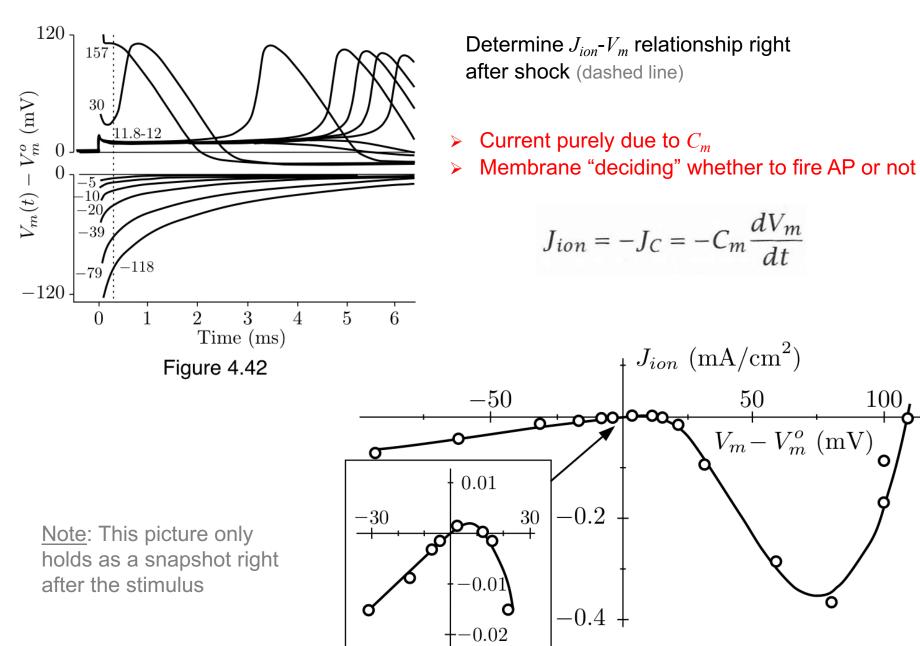
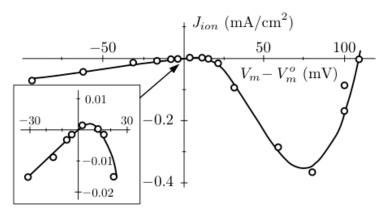


Figure 4.43

50

 $V_m - V_m^o (\mathrm{mV})$ 

100



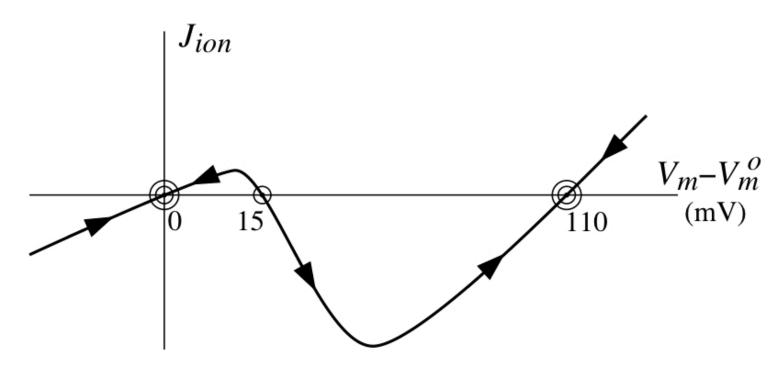


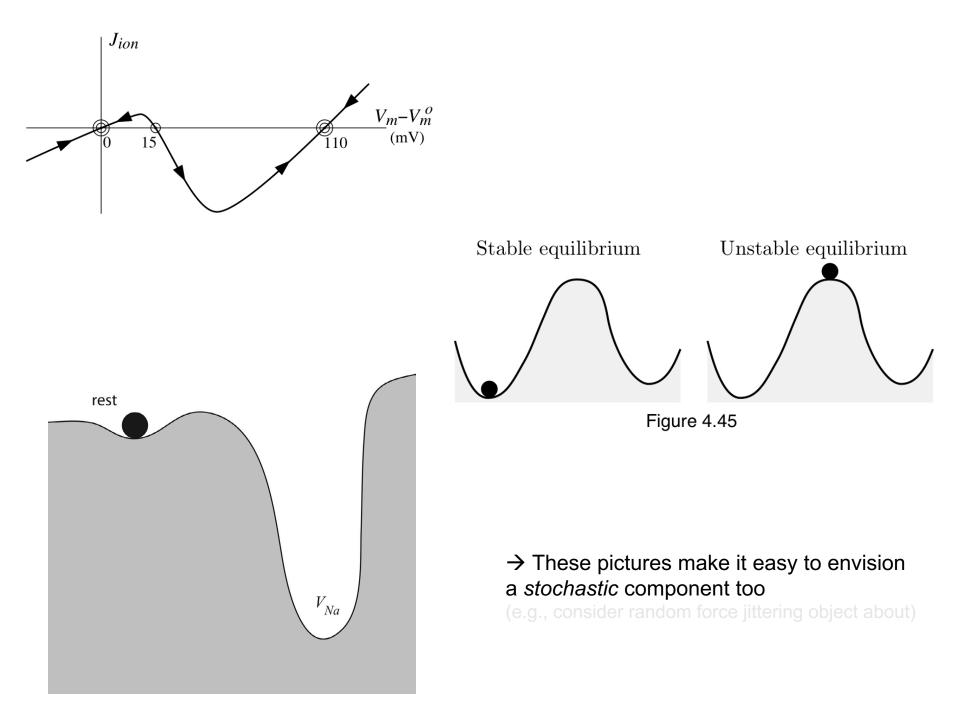
## Equilibrium points

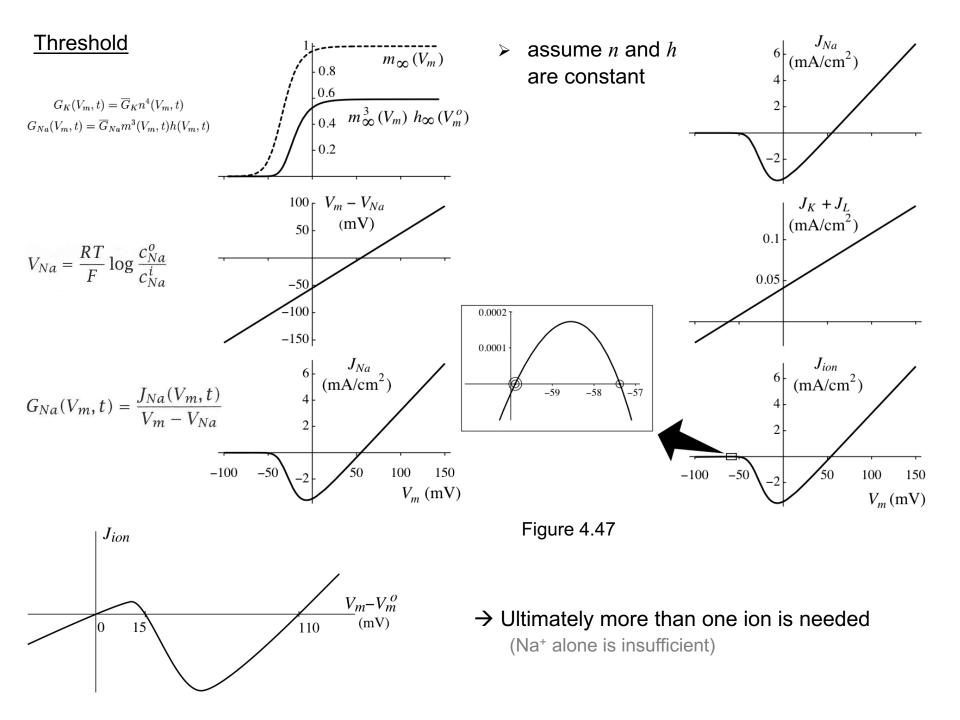
> Stability 
$$J_{ion} = -J_C = -C_m \frac{dV_m}{dt}$$

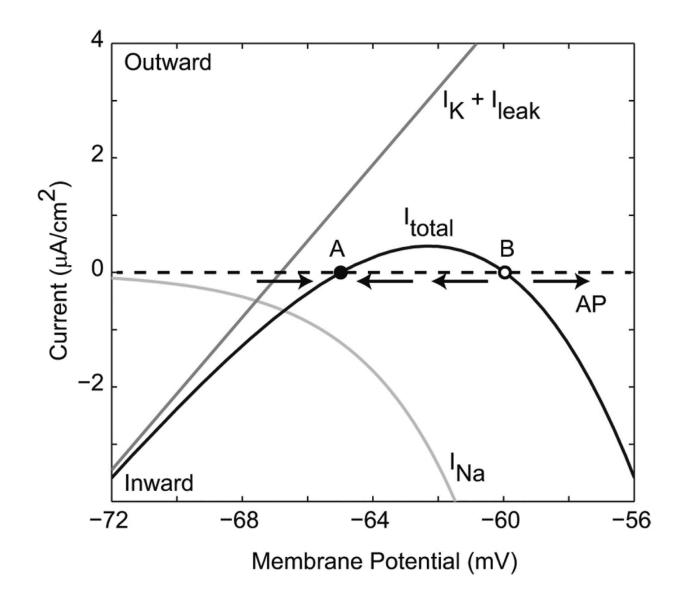
## > Threshold

> Ohm' s Law: Negative resistance?

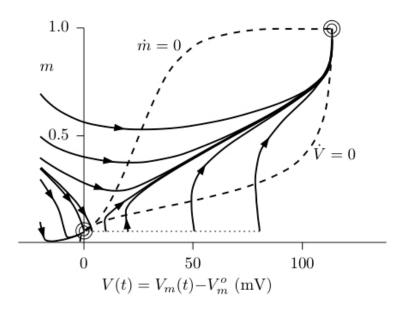








#### Threshold: Phase Plane Portrait



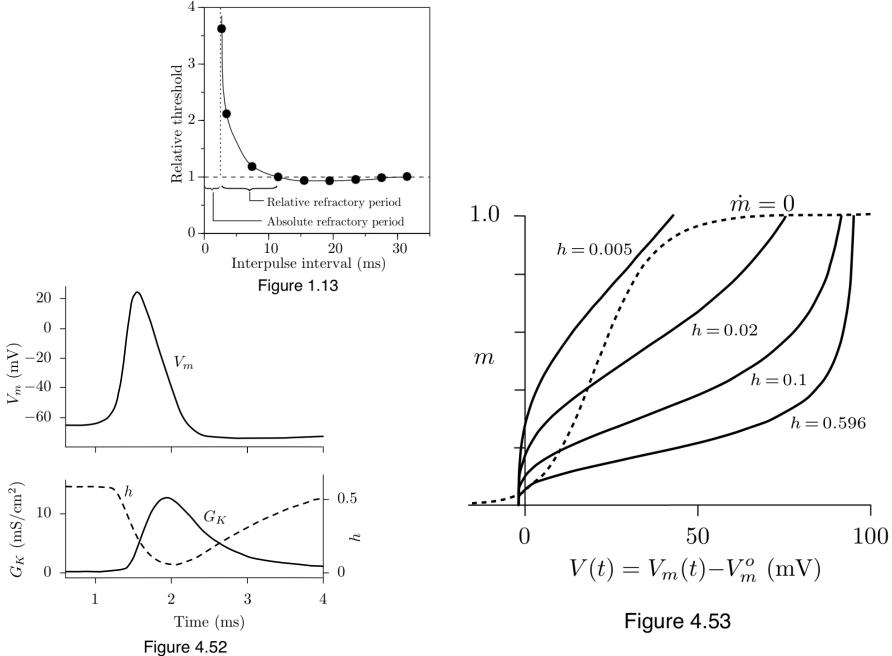
zoomed-in

 $\dot{m} = 0$ ,  $\dot{m} = 0$ ,  $\dot{V} = V_m(t) - V_m^o \text{ (mV)}$ ,

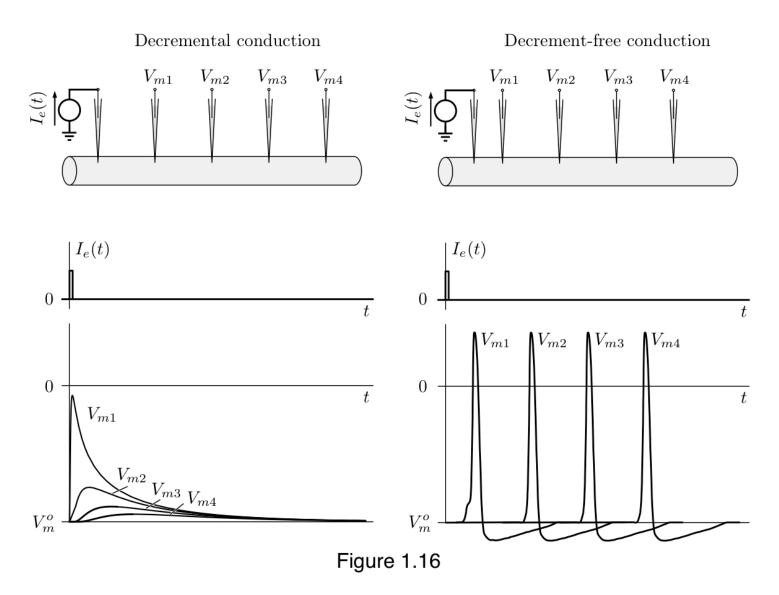
assumes n and h are constant, but m varies dynamically

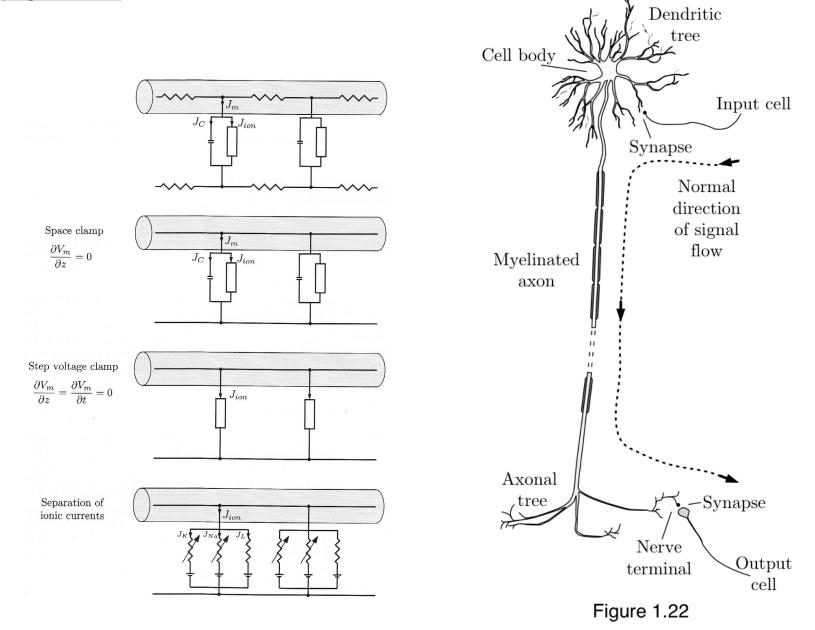


#### **Refractory Period**



# Back to the question of spatial propagation...





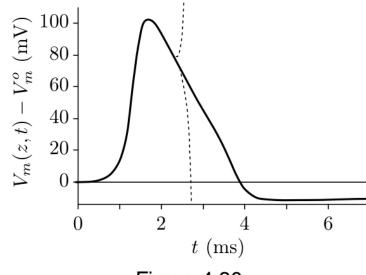
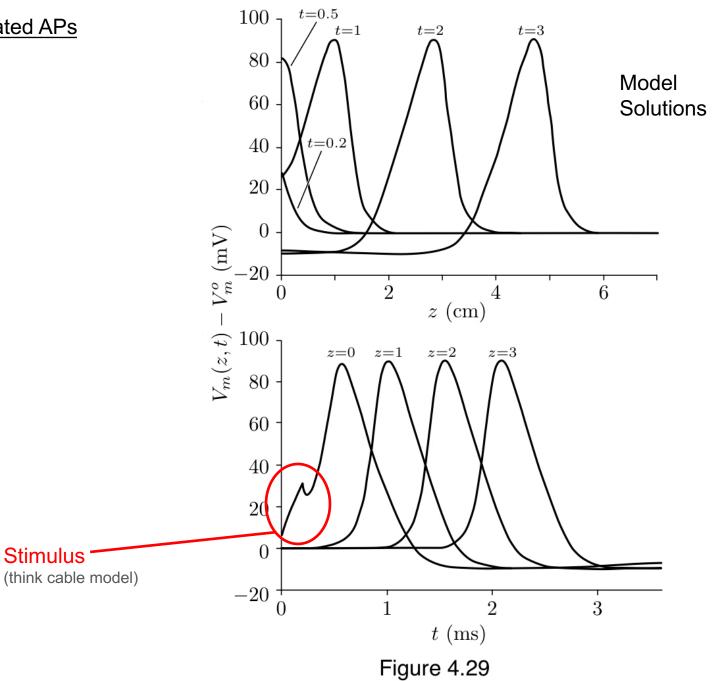


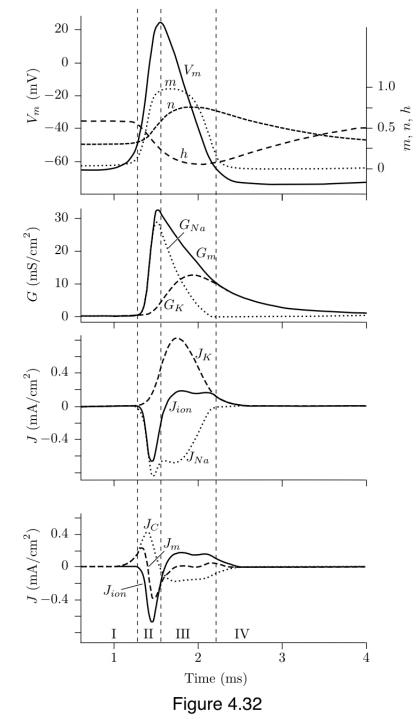
Figure 4.30



 $\begin{bmatrix} 100 \\ 50 \\ 50 \\ 0 \\ 100 \\$ 

# Propagated APs

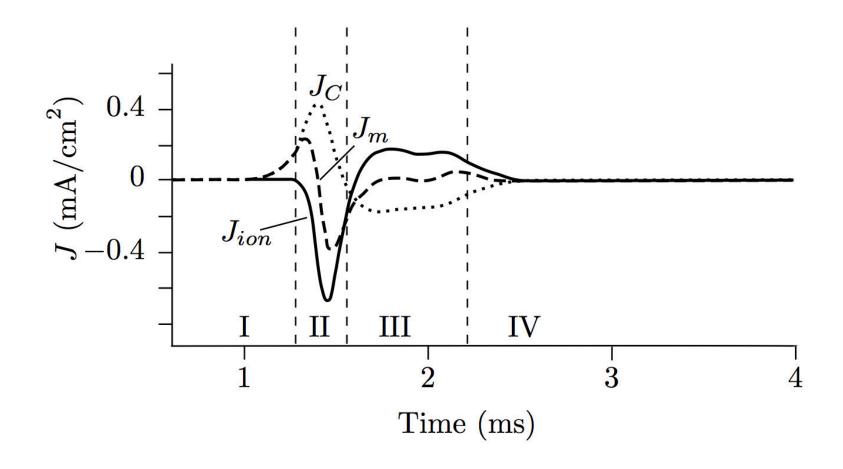




Similar picture as before for propagated AP

 $\rightarrow$  Note lag between  $V_m$  and  $G_m$ 

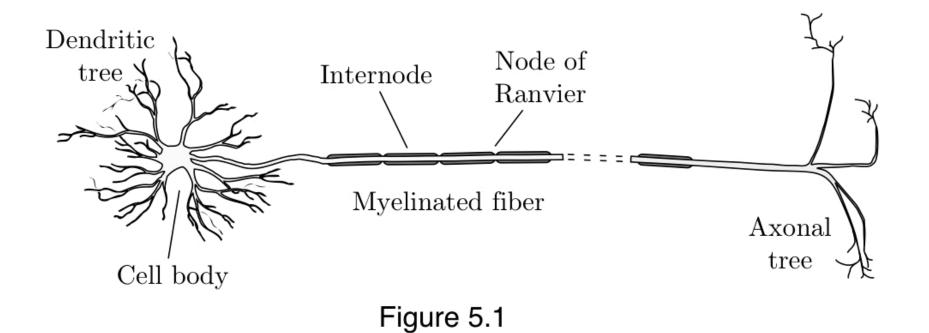
(stems from capacitive surge)

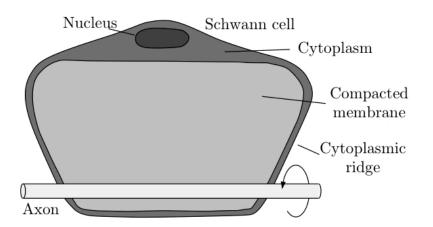


 $\rightarrow$  Note lag between  $V_m$  and  $G_m$ 

(stems from capacitive surge)

#### **Myelination**





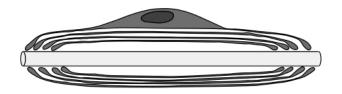




Figure 5.5

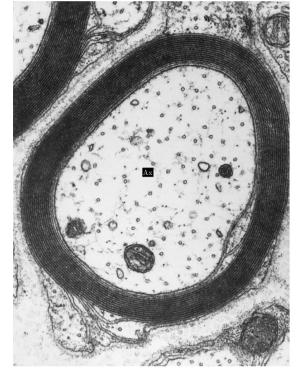


Figure 5.6

